

DMP32D4SW-7 Datasheet



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DiGi Electronics Part Number DMP32D4SW-7-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number DMP32D4SW-7

Description MOSFET P-CH 30V 250MA SOT323

Detailed Description P-Channel 30 V 250mA (Ta) 300mW (Ta) Surface Mo

unt SOT-323



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMP32D4SW-7	Diodes Incorporated
Series:	Product Status:
	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	250mA (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	2.40hm @ 500mA, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
2.4V @ 250μA	1.2 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	51.16 pF @ 15 V
FET Feature:	Power Dissipation (Max):
	300mW (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
SOT-323	SC-70, SOT-323
Base Product Number:	
DMP32	

Environmental & Export classification

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	





30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max @ T _A = +25°C
2017	2.4Ω @ V _{GS} = -10V	-250mA
-30V	4Ω @ V _{GS} = -4.5V	-200mA

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load switches
- Portable applications
- Power management functions

Features

- Low On-Resistance
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

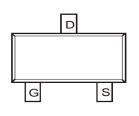
Mechanical Data

- Package: SOT323
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Lead Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe). (3)
- Weight: 0.006 grams (Approximate)

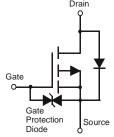




Top View



Top View Pin-out



Equivalent Circuit

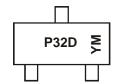
Ordering Information (Note 4)

Γ	Part Number	rt Number Package Marking Reel		Reel Size (inches)	Packing		
	Fait Number	Package	Warking	Reel Size (Iliches)	Qty.	Carrier	
Γ	DMP32D4SW-7	SOT323	P32D	7	3,000	Reel	
ſ	DMP32D4SW-13	SOT323	P32D	13	10,000	Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



P32D = Product Type Marking Code YM = Date Code Marking Y = Year (ex: J = 2022) M = Month (ex: 9 = September)

Date Code Key

Year	2012		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Z		J	K	L	М	N	0	Р	R	S	Т
Month	Jan	Feb	Mar	Apr	Mav	lun	Jul	Aug	Sep	Oct	Nov	Dec
Month	Jan	I CD	IVIAI	Αþi	iviay	Jun	Jui	Aug	Sep	Oct	INOV	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Character	ristic		Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 6)	Vgs = -10V	$T_A = +25$ °C $T_A = +70$ °C	ID	-250 -200	mA
Pulsed Drain Current (Note 6)			Ірм	-1	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation	(Note 5)	D-	300	mW	
Total Power Dissipation	(Note 6)	PD	432		
Thermal Resistance, Junction to Ambient	(Note 5)	D	398		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	290	°C/W	
Thermal Resistance, Junction to Case	(Note 5)	Rejc	142		
Operating and Storage Temperature Range	_	T _J , T _{STG}	-55 to +150	°C	

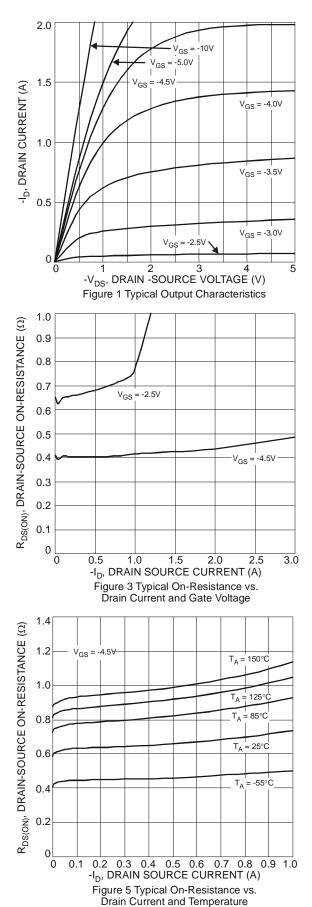
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

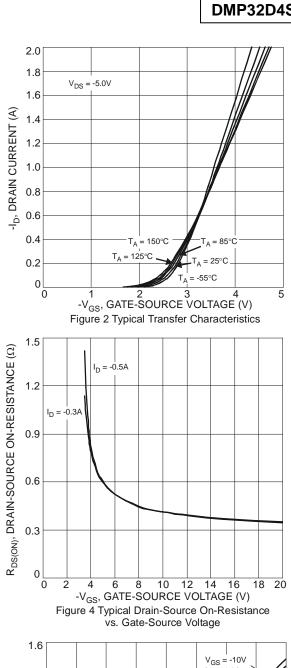
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						•
Drain-Source Breakdown Voltage	BVDSS	-30	_	_	V	$V_{GS} = 0V$, $I_D = -1mA$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	-1	μΑ	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	Igss		_	±10	μA	$V_{GS} = \pm 16V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(TH)	-1.4	_	-2.4	V	$V_{DS} = V_{GS}$, $I_{D} = -250\mu A$
Static Drain-Source On-Resistance	D-s(s)			2.4	Ω	$V_{GS} = -10V, I_{D} = -0.5A$
Static Drain-Source On-Nesistance	R _{DS(ON)}	_		4	12	$V_{GS} = -4.5V$, $I_{D} = -0.3A$
Forward Transfer Admittance	Y _{fs}	_	6	ı	S	$V_{DS} = -10V, I_{D} = -400mA$
Diode Forward Voltage	V_{SD}	_	-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -300mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		51.16	_	pF	15)()()(
Output Capacitance	Coss	_	10.85		рF	V _{DS} = -15V, V _{GS} = 0V, -f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	8.88	ı	pF	1 = 1.001112
Gate Resistance	Rg	_	275	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Qg	_	0.6	_	nC	V _{GS} = -4.5V
Total Gate Charge	Qg	_	1.2	_	nC	V _{DS} = -10V,
Gate-Source Charge	Qgs	_	0.2	_	nC	$V_{GS} = -10V$ $I_{D} = -1A$
Gate-Drain Charge	Qgd	_	0.3	_	nC]
Turn-On Delay Time	t _{D(on)}	_	9.86	_	ns	
Turn-On Rise Time	t _r	_	11.5	_	ns	V _{DS} = -15V, I _D = -1A
Turn-Off Delay Time	t _{D(off)}		31.8	_	ns	$V_{GS} = -10V$, $R_{G} = 6\Omega$
Turn-Off Fall Time	tf		21.9	_	ns	

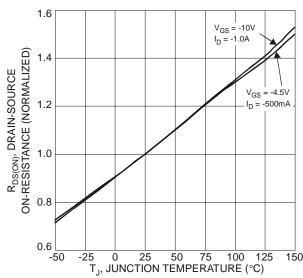
Notes:

- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.











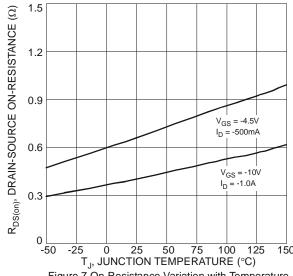
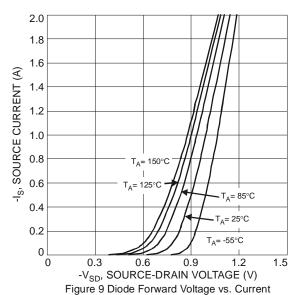


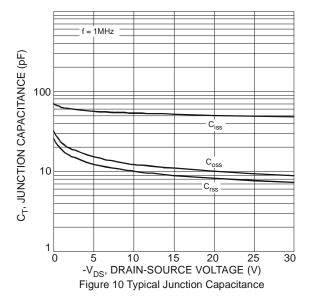
Figure 7 On-Resistance Variation with Temperature



10 -V_{GS}, GATE-SOURCE VOLTAGE (V) I_D = -1A 0 2 0.4 0.6 0.8 1.0 Q_g, TOTAL GATE CHARGE (nC) 1.2 Figure 11 Gate-Charge Characteristics

2.6 VGS(TH), GATE THRESHOLD VOLTAGE (V) 2.4 2.2 -I_D=1mA 2.0 1.8 $-I_D = 250\mu A$ 1.6 1.4 5 0 25 50 75 100 125 T_A, AMBIENT TEMPERATURE (°C) -50

Figure 8 Gate Threshold Variation vs. Ambient Temperature

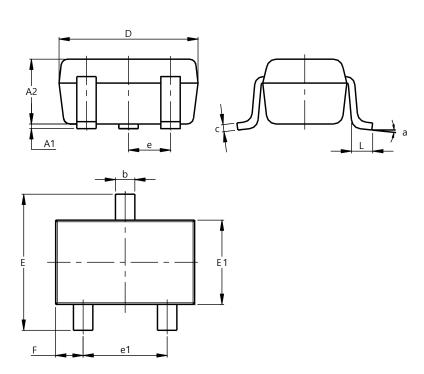




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323

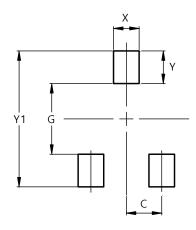


SOT323								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.25	0.40	0.30					
С	0.10	0.18	0.11					
D	1.80	2.20	2.15					
Е	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	C).650 B	SC					
e1	1.20	1.40	1.30					
F	0.375	0.475	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323



Dimensions	Value
	(in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500



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